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Vishay Siliconix

# Automotive N-Channel 80 V (D-S) 175 °C MOSFET

# PowerPAK® SO-8L

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0030			
I <sub>D</sub> (A)	248			
Configuration	Single			
Package	PowerPAK SO-8L			

**Bottom View** 

Top View

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics</li>
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



$Q^D$	
GO-	
N-Channel MOSFET	

ABSOLUTE MAXIMUM RATINGS (T	$T_C = 25  ^{\circ}C$ , unles	s otherwise noted	)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	80	V	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C	1	248		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	143		
Continuous source current (diode conduction)	Is	248	Α		
Pulsed drain current		I <sub>DM</sub>	420		
Single pulse avalanche current		I <sub>AS</sub>	42		
Single pulse avalanche energy		E <sub>AS</sub>	88	mJ	
Maximum navvar discination	T <sub>C</sub> = 25 °C	D	500	W	
Maximum power dissipation	T <sub>C</sub> = 125 °C	$P_{D}$	166	VV	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) <sup>b</sup>			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount a	$R_{thJA}$	42	°C/W
Junction-to-case (drain)		$R_{thJC}$	0.3	C/VV

#### Notes

- a. When mounted on 1" square PCB (FR4 material)
- b. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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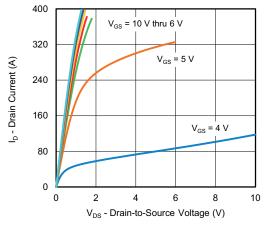
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0, I_D = 250 \mu A$		80	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.2	2.7	3.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V	-	-	10	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0025	0.0030	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0059	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0075	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	82	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>			-	4746	6645	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	814	1140	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	51	72	
Total gate charge <sup>c</sup>	Qg			-	78	117	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 40 \text{ V}, I_{D} = 10 \text{ A}$	-	18	-	nC
Gate-drain charge c	$Q_{gd}$			-	16	-	
Gate resistance	Rg		f = 1 MHz	0.5	1.0	1.50	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	16	20	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{\mathrm{DD}}$	= 40 V, $R_L = 4 \Omega$	-	10	15	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A},$	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		39	50	ns
Fall time <sup>c</sup>	t <sub>f</sub>				9	15	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						•
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	420	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>			-	50	65	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		-	71	95	nC
Reverse recovery fall time	t <sub>a</sub>			-	28	44	
Reverse recovery rise time	t <sub>b</sub>	7		-	22	38	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	2.4	3.6	Α

#### Notes

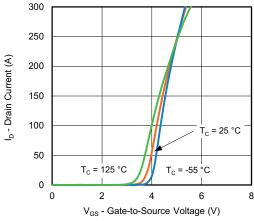
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

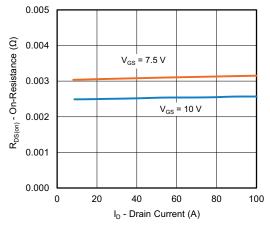




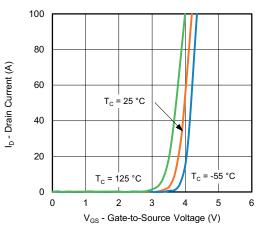
#### **Output Characteristics**



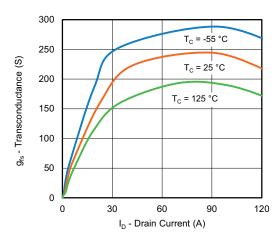
Transfer Characteristics



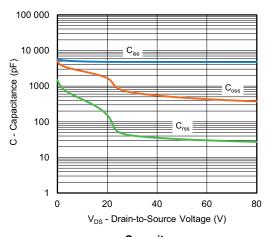
On-Resistance vs. Drain Current



**Transfer Characteristics** 

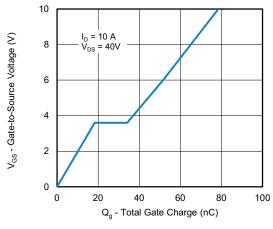


Transconductance

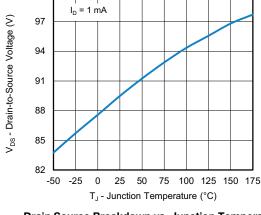


Capacitance



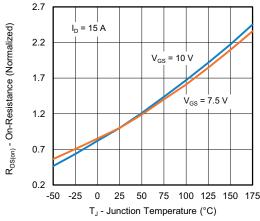


**Gate Charge** 

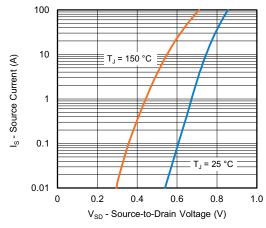


100

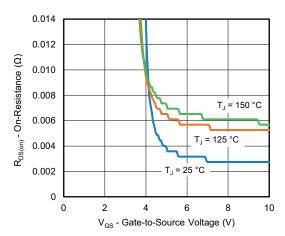
**Drain Source Breakdown vs. Junction Temperature** 



On-Resistance vs. Junction Temperature

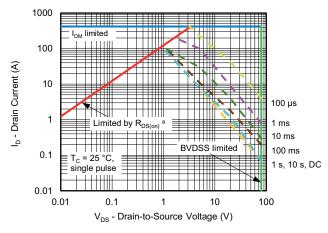


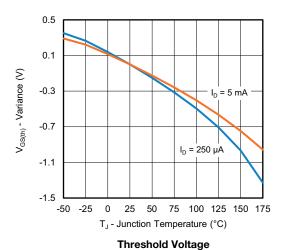
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to Source Voltage





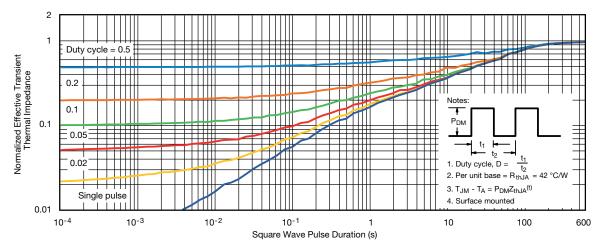


#### Safe Operating Area

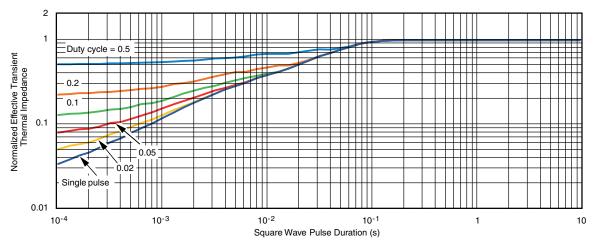
#### Note

a.  $V_{GS} > minimum V_{GS}$  at which  $R_{DS(on)}$  is specified





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

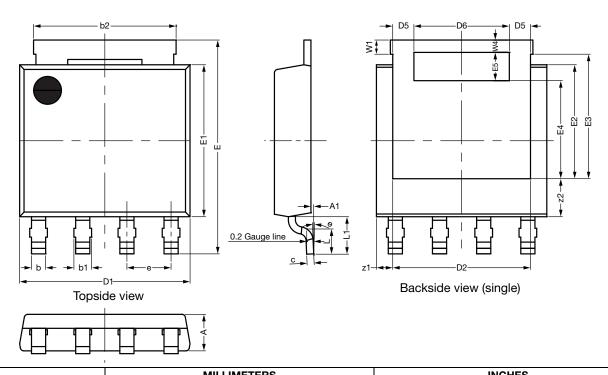
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77297.

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# PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

#### ECN: C22-1223-Rev. C, 19-Dec-2022 DWG: 6067

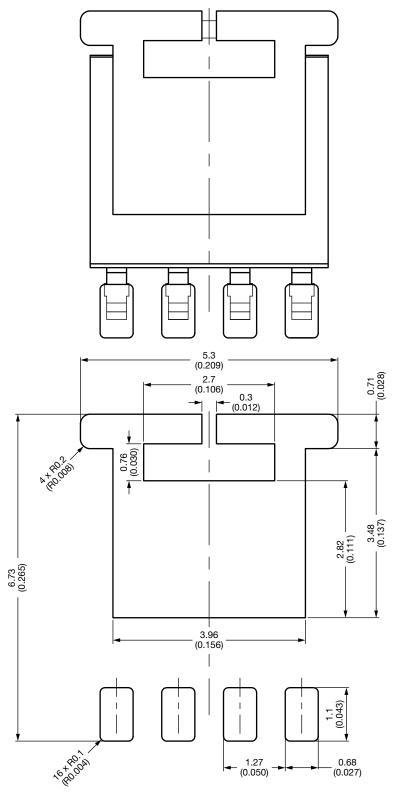
#### Note

Millimeter will govern

Revison: 19-Dec-2022 1 Document Number: 76666



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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